Cryo-CMOS Transceivers for Control and Readout of Semiconductor Spin Qubits

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Outline

- Need for cryogenic electronics for scalable quantum computers
 - Associated challenges
- Introducing control and readout principles for spin qubits
- Cryo-CMOS controller for spin qubits
 - Behavior of active and passive CMOS devices at cryogenic temperatures
 - Required circuit and system specification
 - Controller architecture and circuit implementation
 - Electrical characterization
 - Experiments with qubits (single- and two-qubit operations)
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- Conclusions

General Block Diagram of a Quantum Computer

Electronic interface (Control & Readout)





[J. Bardin, ISSCC'23]

What Can We Learn from History?

- Miniaturization Vacuum tube to transistors
- Integration Transistor to Integrated Circuit



ENIAC (Vacuum tube) **Integrated Circuit**

Silicon-based computers

Need for cryogenic electronics



Challenges

- What kinds of functionalities are needed for qubit control and readout?
- System & circuit specifications?
 - Linearity, noise, jitter,...
- Cryogenic technology?
 - How does commercial CMOS perform at 4K? Transistor model?
- Demanding spec with limited power consumption?
- Cryogenic measurements?
- Measurements with Qubits?



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Required Functionalities for running a Quantum Algorithm



Spin Qubit Operation– Initialization





- Behavior of double quantum dot → dependent on the voltage of the plunger gates (V_{LP}, V_{RP})
- (N_L, N_R) → Electron population on the left and right dots

Single-Qubit Operation



Frequency Multiplexing Technique for Qubit Control



Two-Qubit Gate



- No interaction between qubits
- Suitable for single-qubit operation

- Enabling qubit-1 and qubit-2 interaction by applying a voltage pulse on barrier gate
- Controlled-Not (CNOT) \rightarrow XOR

 $\begin{cases} Q_1 = |0\rangle \rightarrow Q_2 \text{ unchanged} \\ Q_1 = |1\rangle \rightarrow Q_2 \text{ flipped} \end{cases}$

Spin Qubit Operation– Manipulation











Gate-based Readout



Required Building Blocks



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Modeling: Cryo-CMOS Benefits and Constraints

	Parameter	Behavior
1	Threshold voltage	Increases by ~100mV
2	Mobility	Increases
3	Saturated velocity	Increases by 40%
4	Transconductance	increases
5	G_m/I_D in saturation	No change
6	G _m /I _D in weak-inversion	Up to 3x improvement
7	Subthreshold swing	Decreases but not proportionally to temp.
8	Leakage current	Reduces substantially
9	device output resistance	decreases by 50%
10	device intrinsic gain	Almost the same
11	Switch ON-resistance	~50% reduction

	Parameter	Behavior
12	Gate resistance	~50% reduction
13	Device parasitic cap.	Almost the same
14	f _t and f _{max}	40% increase
15	Device matching	worse
16	A_{vth}, A_{β}	25% increase
17	Thermal conductivity	No change (maximizes at 20K)
18	Self heating	Much more serious
19	Thermal noise	Reduces but not proportionally to temp
20	Flicker noise	Almost the same
21	Ind. & cap. value	Almost the same
22	Cap. Q-factor	3x improvement <10GHz
23	Ind. Q-factor	2.5x improvement

Emulating Qubit Behavior



System-Level Specifications



Controller Architecture



Controller Architecture



Numerically-Controlled Oscillator (NCO)



$$n_{NCO} > \log_2 \frac{f_S}{2f_R \sqrt{1-F}} \xrightarrow{F=99.99\%, f_R=1MHz} \boxed{n_{NCO} \ge 17 - \text{bit}}$$

Phase-to-Amplitude Conversion



Need for Amplitude & Phase Modulation



Deriving Frequency Multiplexed Qubits



- Intermittent sequential operations on any qubit demand keeping track of the phase of all qubits.
- Consequently, an individual reference clock would be required for each qubit.
- NCO outputs are time-multiplexed to allow operation on one qubit at a time to reduce system.

Simultaneous Qubit Operation



• Corresponding signal of two qubits can be generated simultaneously.

LO Feedthrough and Image Problems



$$IIR \approx \frac{4}{\epsilon^2 + \Delta\theta^2} \xrightarrow{IIR \gg 50 dB} \begin{cases} \Delta\theta \ll 0.3^\circ \\ \epsilon \ll 0.5\% \end{cases}$$

LO Feedthrough and Image Cancellation



- α_{I} and α_{Q} for compensating for gain imbalance.
- β_I and β_Q for compensating for phase imbalance.
- $\gamma_{\rm I}$ and $\gamma_{\rm Q}$ for cancelling LO leakage.

System Architecture



Controller

Transmitter















Chip Micrograph & Self heating



Power consumption (W)

Experimental results – Pulse Shaping



Initialization













Simultaneous Rabi Oscillation on Two Qubits



Generate two-tone signal with Horse Ridge





Towards Two-Qubit Gate Operation



A Cryo-CMOS-Driven Quantum Algorithm



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Proposed RX Architecture



• High-IF RX architecture

- Avoid higher 1/f noise at cryogenic temperatures, thus maintaining the qubits SNR over the entire bandwidth
- Slightly increasing the power consumption of IF amplifiers and ADCs

RX Schematic





[B. Prabowo, ISSCC'21]

Chip Micrograph & Power Consumption





• Total power of 66mW at 4K

RX Characterizations at 300K & 4K



- ~5 dB gain increase at 4K
 - Increase in mobility
 - Increase in Q factor

- ~5x NF reduction
 - Shot noise
 - Self-heating effect

- 16-QAM -70 dBm input
- 200 MHz Baseband LPF

Measurement Setup



• A traveling-wave parametric amplifier (TWPAR) and a HEMT LNA are used in the readout chain not to limit the inherent qubit SNR.

Readout Setup

Installed copper enclosure







Image: state stat

4K Plate

Mixing Chamber

Measured Charge Stability Diagram



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[The Economist, 20th Jun 2015]

Cryo-CMOS: Betting on the winning horse





Spin qubits



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Thank You for Your Attention!